

# μPA2813T1L

P-channel MOSFET

-30 V, -27 A, 6.2 mΩ

R07DS0763EJ0102

Rev.1.02

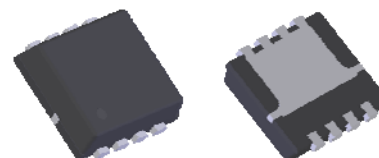
May. 28, 2013

## Description

The μPA2813T1L is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

## Features

- $V_{DSS} = -30\text{ V}$  ( $T_A = 25^\circ\text{C}$ )
- Low on-state resistance  
—  $R_{DS(on)} = 6.2\text{ m}\Omega\text{ MAX.}$  ( $V_{GS} = -10\text{ V}$ ,  $I_D = -27\text{ A}$ )
- 4.5 V Gate-drive available
- Small & thin type surface mount package with heat spreader
- Pb-free and Halogen free



8-pin HVSON(3333)

## Ordering Information

Part No.	Lead Plating	Packing	Package
μPA2813T1L-E2-AT *1	Pure Sn	Tape 3000 p/reel	8-pin HVSON (3333) typ. 0.028 g

Note: \*1. Pb-free (This product does not contain Pb in external electrode and other parts.)

## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to Source Voltage ( $V_{GS} = 0\text{ V}$ )	$V_{DSS}$	-30	V
Gate to Source Voltage ( $V_{DS} = 0\text{ V}$ )	$V_{GSS}$	±20	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	±27	A
Drain Current (pulse) *1	$I_{D(pulse)}$	±108	A
Total Power Dissipation *2	$P_{T1}$	1.5	W
Total Power Dissipation (PW = 10 sec) *2	$P_{T2}$	3.8	W
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{T3}$	52	W
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C
Single Avalanche Current *3	$I_{AS}$	23	A
Single Avalanche Energy *3	$E_{AS}$	54	mJ

## Thermal Resistance

Channel to Ambient Thermal Resistance *2	$R_{th(ch-A)}$	83.3	°C/W
Channel to Case (Drain) Thermal Resistance	$R_{th(ch-C)}$	2.4	°C/W

Notes: \*1.  $PW \leq 10\ \mu\text{s}$ , Duty Cycle  $\leq 1\%$

\*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mm

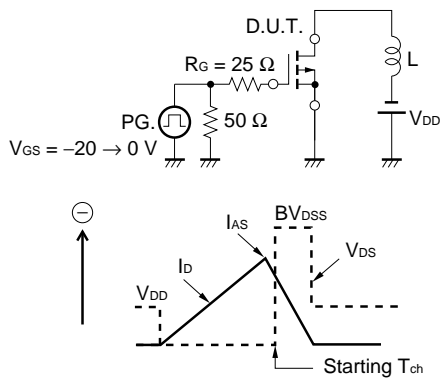
\*3. Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = -15\text{ V}$ ,  $R_G = 25\ \Omega$ ,  $V_{GS} = -20 \rightarrow 0\text{ V}$ ,  $L = 100\ \mu\text{H}$

**Electrical Characteristics (T<sub>A</sub> = 25°C)**

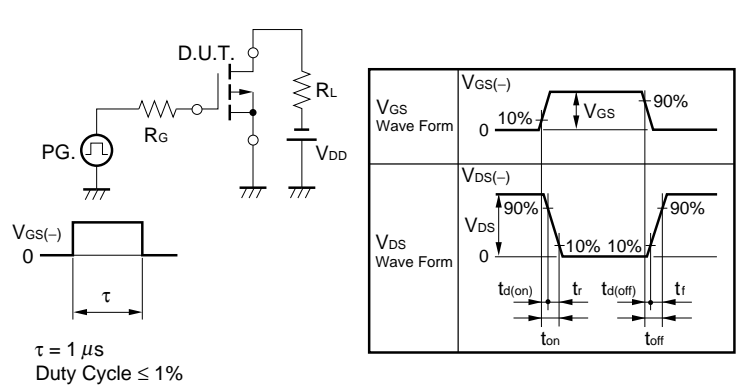
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1	μA	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V
Gate Leakage Current	I <sub>GSS</sub>			±100	nA	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V
Gate Cut-off Voltage	V <sub>GS(off)</sub>	-1.0		-2.5	V	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA
Forward Transfer Admittance *1	y <sub>fs</sub>	8.0			S	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -13.5 A
Drain to Source On-state Resistance *1	R <sub>DS(on)1</sub>		4.8	6.2	mΩ	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -27 A
	R <sub>DS(on)2</sub>		9	13	mΩ	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -13.5 A
Input Capacitance	C <sub>iSS</sub>		3130		pF	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz
Output Capacitance	C <sub>oSS</sub>		1490		pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>		1290		pF	
Turn-on Delay Time	t <sub>d(on)</sub>		16		ns	V <sub>DD</sub> = -15 V, I <sub>D</sub> = -13.5 A, V <sub>GS</sub> = -10 V, R <sub>G</sub> = 10 Ω
Rise Time	t <sub>r</sub>		41		ns	
Turn-off Delay Time	t <sub>d(off)</sub>		196		ns	
Fall Time	t <sub>f</sub>		234		ns	
Total Gate Charge	Q <sub>G</sub>		80		nC	V <sub>DD</sub> = -24 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -27 A
Gate to Source Charge	Q <sub>GS</sub>		9		nC	
Gate to Drain Charge	Q <sub>GD</sub>		42		nC	
Body Diode Forward Voltage *1	V <sub>F(S-D)</sub>		0.9		V	I <sub>F</sub> = 27 A, V <sub>GS</sub> = 0 V
Reverse Recovery Time	t <sub>rr</sub>		173		ns	I <sub>F</sub> = 27 A, V <sub>GS</sub> = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q <sub>rr</sub>		270		nC	

Note: \*1. Pulsed

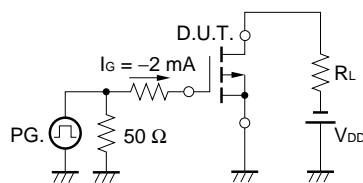
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



**TEST CIRCUIT 2 SWITCHING TIME**

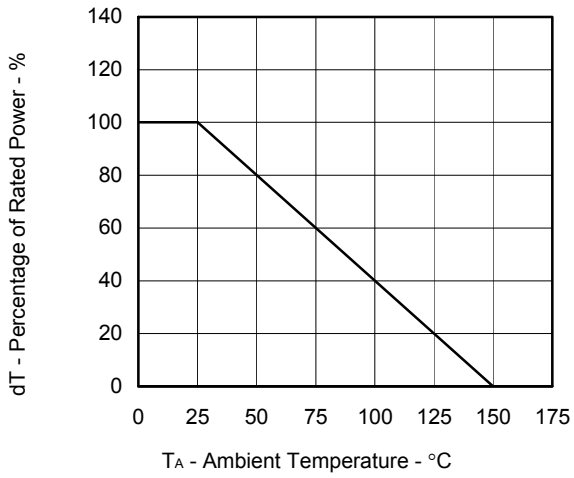


**TEST CIRCUIT 3 GATE CHARGE**

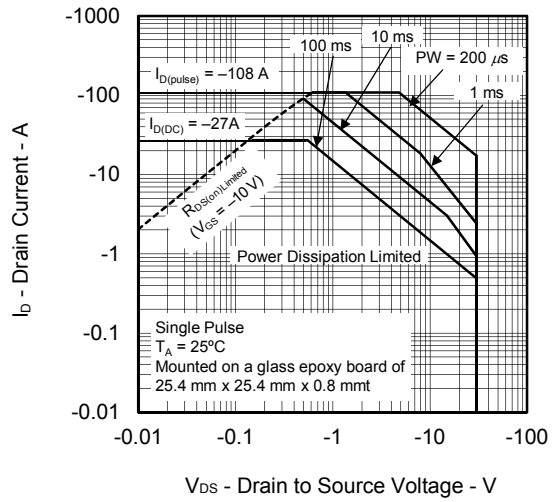


Typical Characteristics (T<sub>A</sub> = 25°C)

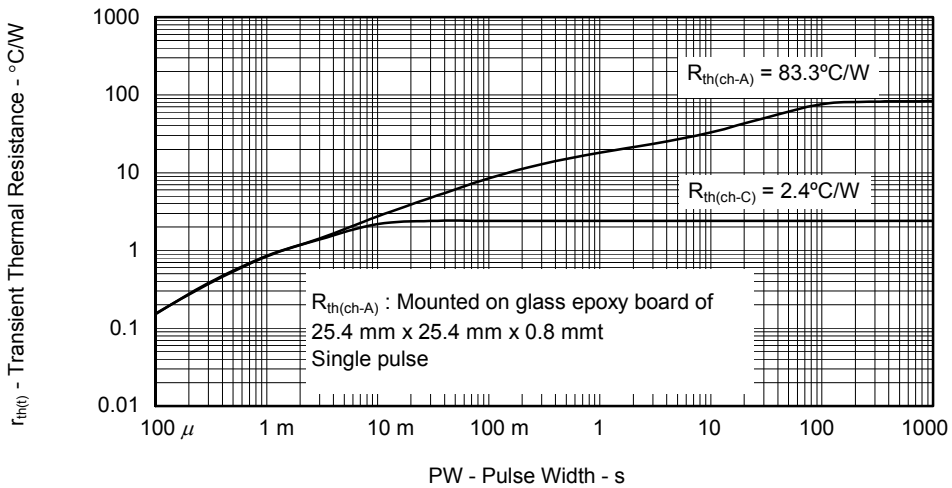
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



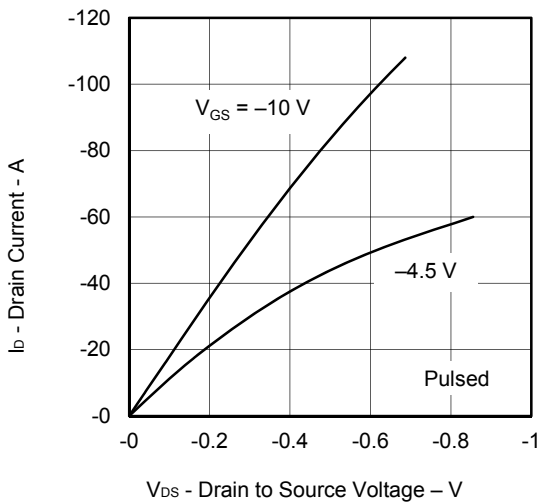
FORWARD BIAS SAFE OPERATING AREA



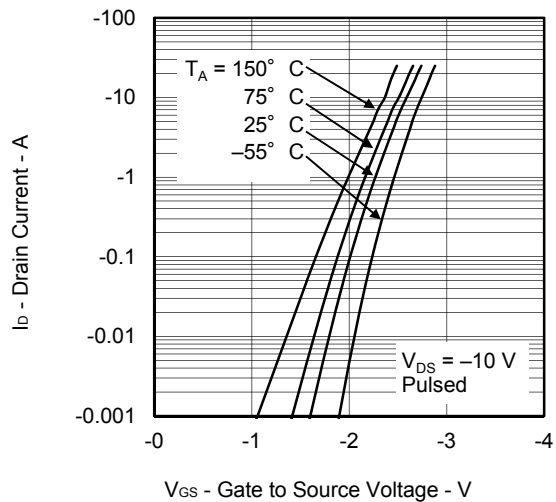
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



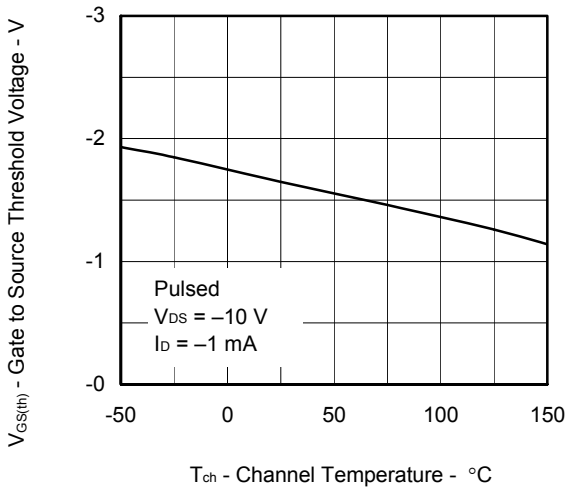
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



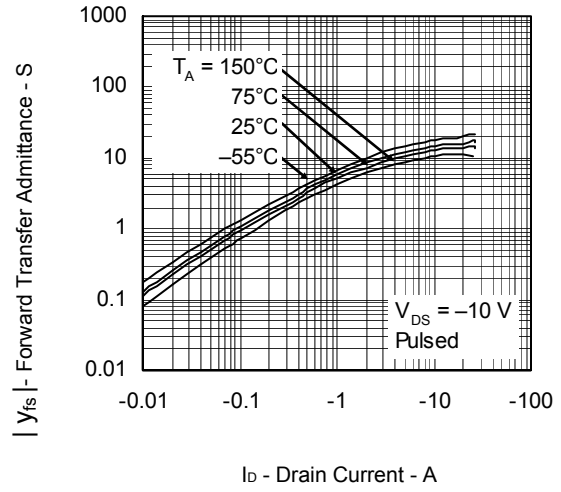
FORWARD TRANSFER CHARACTERISTICS



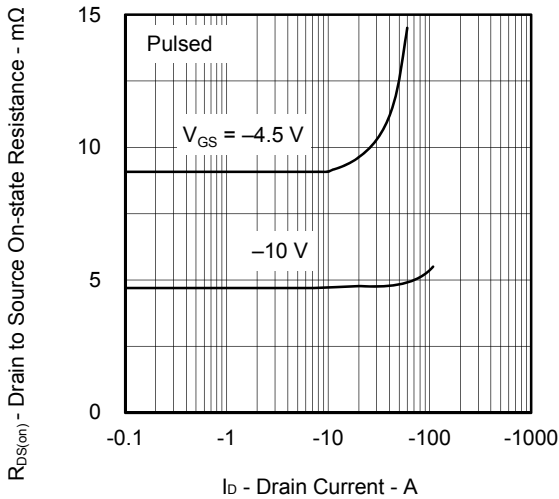
GATE CUT-OFF VOLTAGE vs.CHANNEL TEMPERATURE



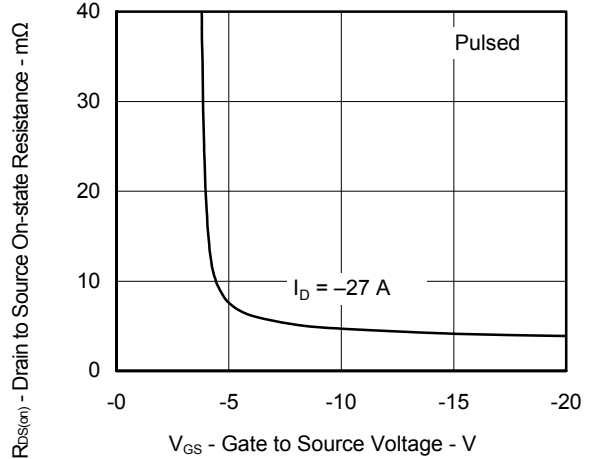
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



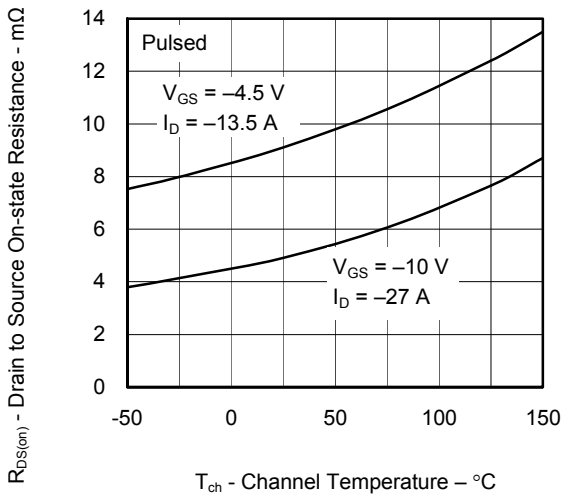
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



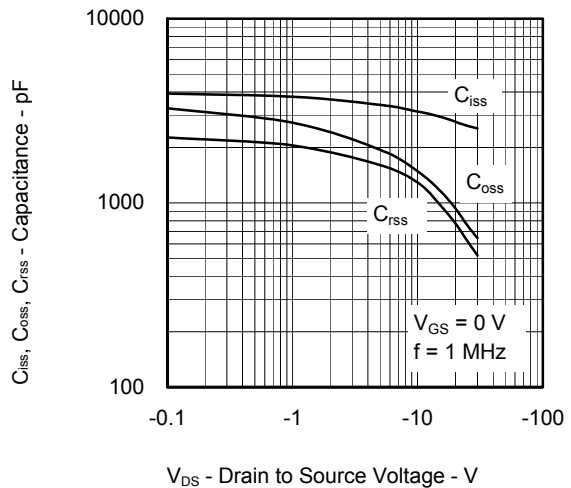
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



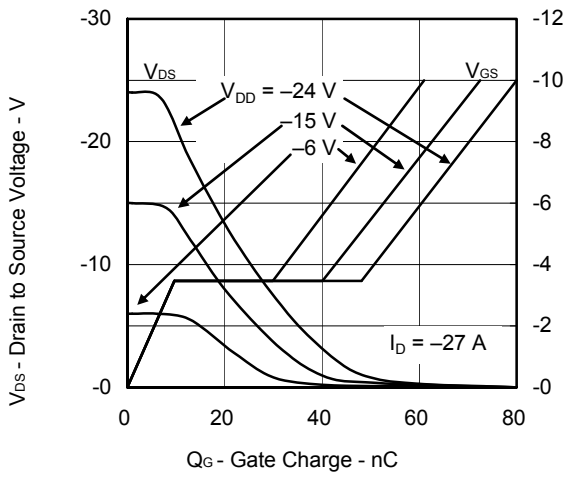
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



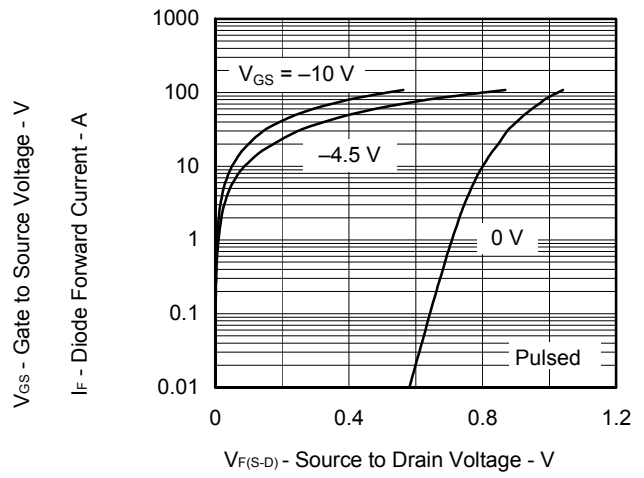
CAPACITANCE vs. DRAIN TOSOURCE VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS

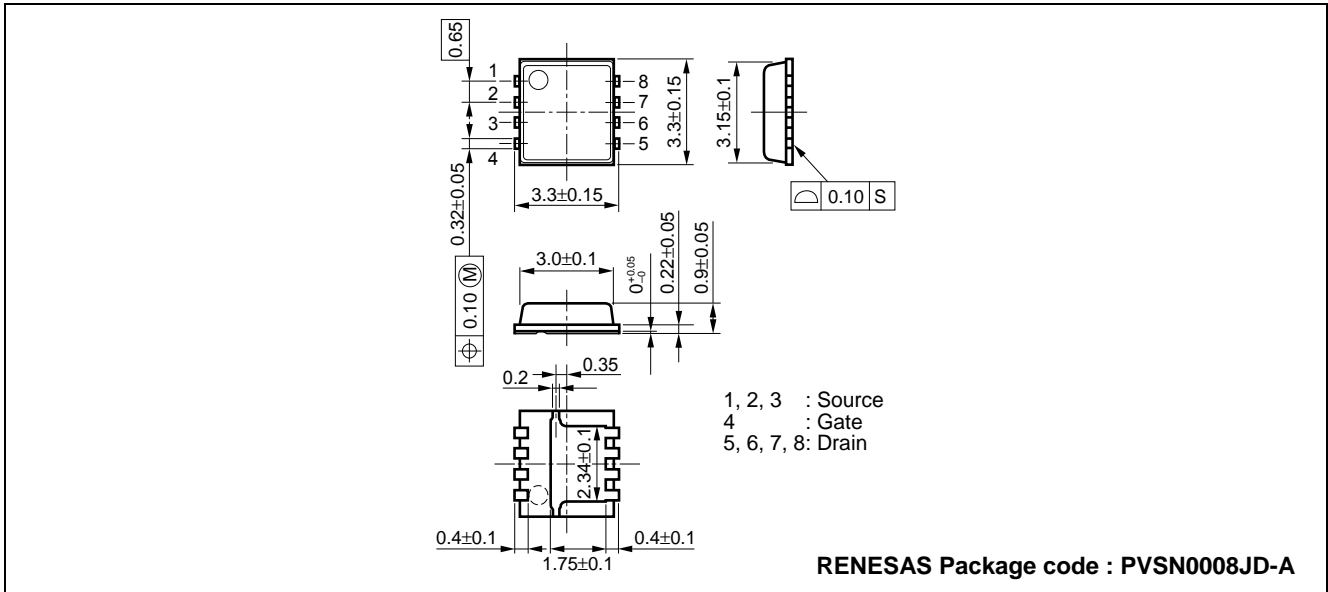


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

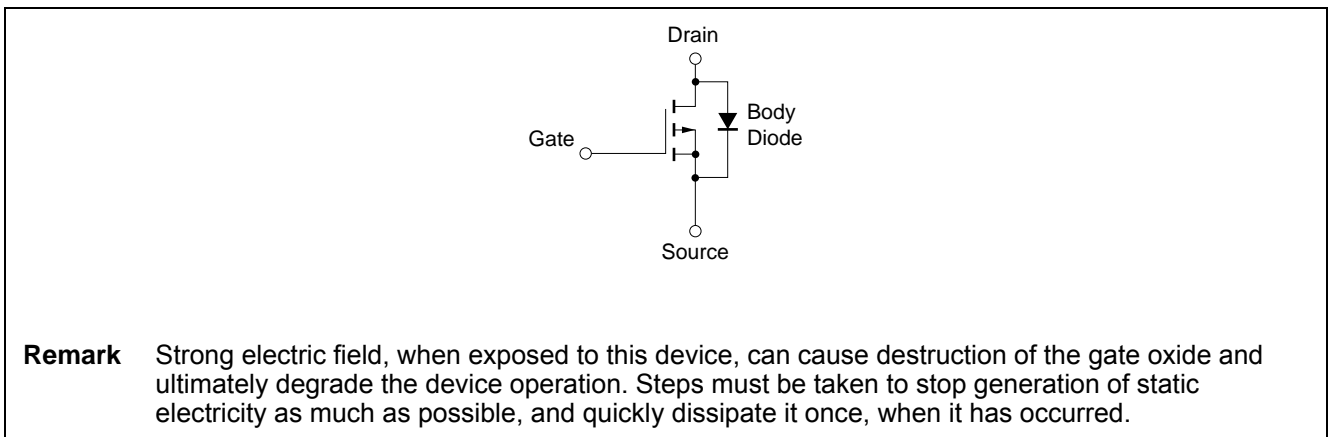


### Package Drawings (Unit: mm)

#### 8-pin HVSON (3333)



### Equivalent Circuit



**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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**Renesas Electronics Canada Limited**  
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada  
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**Renesas Electronics Europe Limited**  
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: +44-1628-651-700, Fax: +44-1628-651-804

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Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-65030, Fax: +49-211-6503-1327

**Renesas Electronics (China) Co., Ltd.**  
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Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

**Renesas Electronics (Shanghai) Co., Ltd.**  
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China  
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

**Renesas Electronics Hong Kong Limited**  
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

**Renesas Electronics Taiwan Co., Ltd.**  
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**Renesas Electronics Singapore Pte. Ltd.**  
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